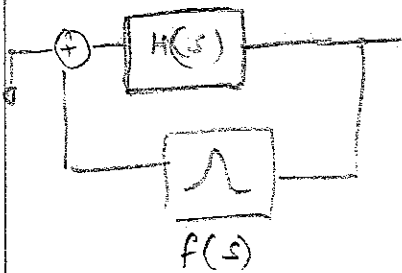


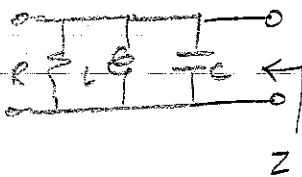
L-C Oscillators:



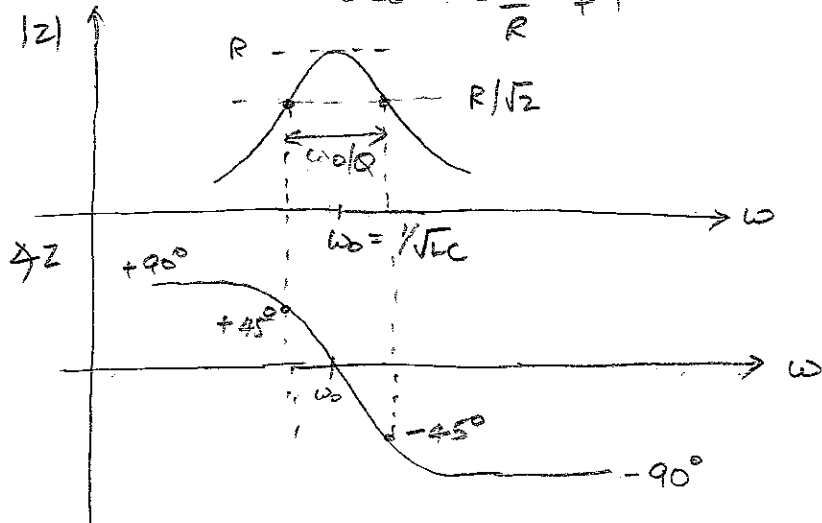
- LC network gives frequency selectivity
- stabilizes frequency of oscillation
- Barkhausen criterion:
 - Loop gain $T(s) = H(s)f(s)$
 - For oscillation at frequency $\omega = \omega_{osc}$

$$|T(j\omega_{osc})| = 1 \text{ and } \angle T(j\omega_{osc}) = 360^\circ$$

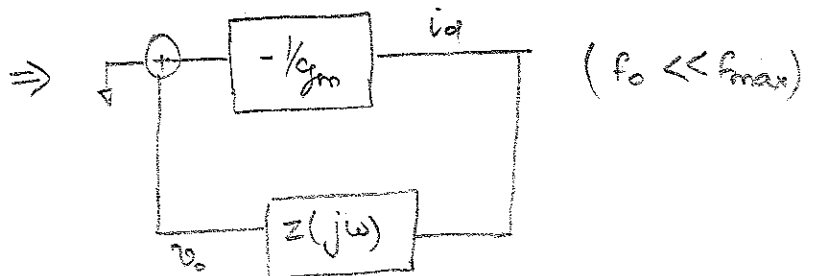
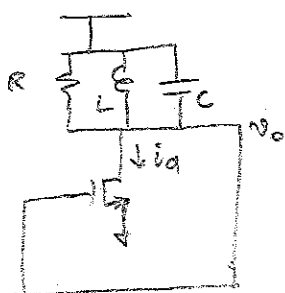
- Although we can build oscillators without R's, these oscillators have poor performance compared to LC oscillators.
- Parallel L-C tank:



$$Z(j\omega) = \frac{sL}{LCs^2 + \frac{sL}{R} + 1}$$

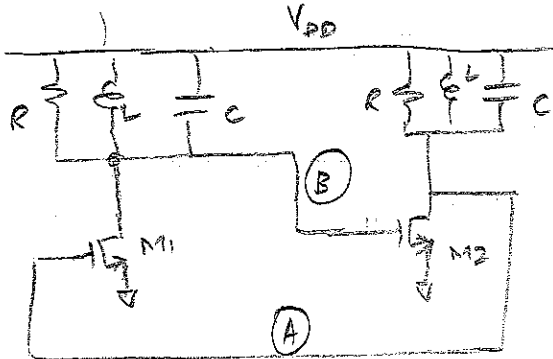


- Now consider



- At resonance, RLC tank contributes 0 phase-shift
- FET contributes 180° phase shift for frequencies $f \ll f_c$.
- \Rightarrow total phase shift = $180^\circ \Rightarrow$ no oscillations.

• Next, consider



At $f_0 = \frac{1}{2\pi\sqrt{LC}}$, each

tuned stage contributes 180° phase-shift

\Rightarrow total $\phi = 360^\circ$

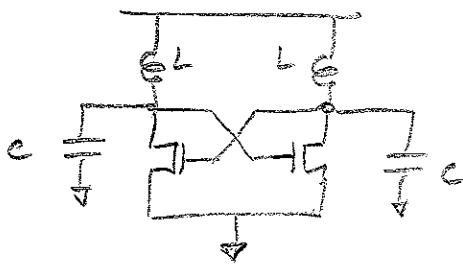
\Rightarrow oscillations possible

if $|T(j\omega_0)| \geq 1$

or $(g_m R)^2 \geq 1$

• This is the core of most on-chip LC oscillators

Also drawn as:

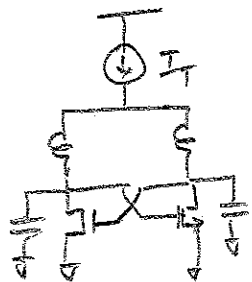
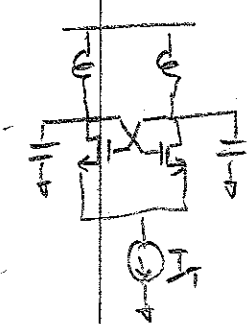


Note that at $f = f_0$, (A) and (B) must be exactly

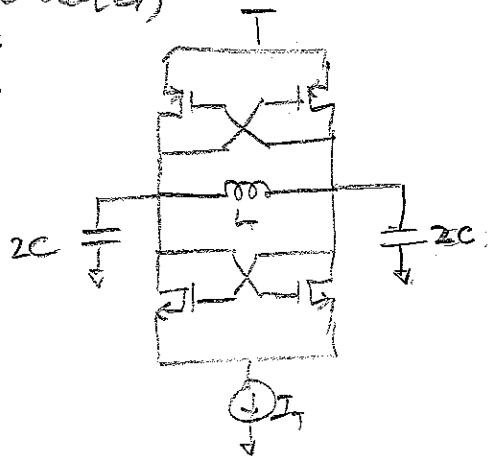
180° out of phase

\Rightarrow differential outputs for free.

Other implementations: (more later)



I_T stabilizes amplitude of oscillation

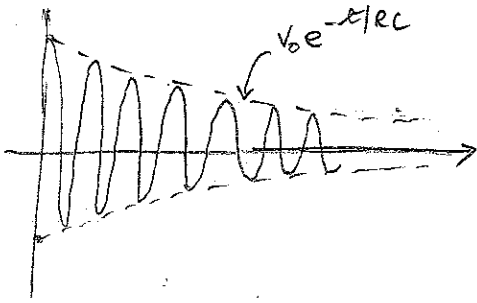
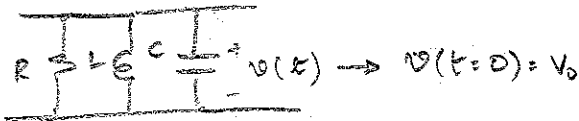


Complementary cross-coupled oscillator

\Rightarrow Current re-use gives more g_m

One-port view of oscillators:

- Consider a parallel R-L-C tank with an initial voltage V_0 across the capacitor.

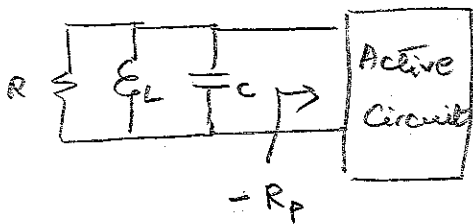


$$\text{If } Q = \frac{R}{\omega_0 L} = \sqrt{\frac{L}{C}} = \frac{1}{\omega_0 R C} > \frac{1}{2},$$

the voltage will be an exponentially decaying sinusoid of freq. ω_0 and amplitude $V_0 e^{-t/RC}$.

\Rightarrow Amplitude decays with time constant $\tau = RC$

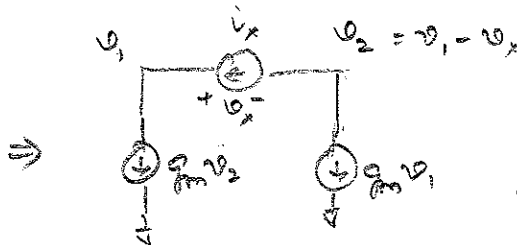
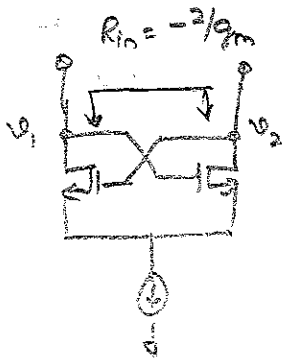
- As we make $R \rightarrow \infty$, τ becomes larger, and in the limit, the amplitude never decays. (i.e. this is an ideal L-C tank)
- Suppose we have an active circuit that introduces a "negative-R" in parallel with R:



\Rightarrow Amplitude envelope is now

$$V_0 \exp\left[-\frac{t}{(R-R_p)C}\right]$$

\Rightarrow If $R = R_p$, amplitude never decays



$$i_x = g_m v_2 = -g_m v_1$$

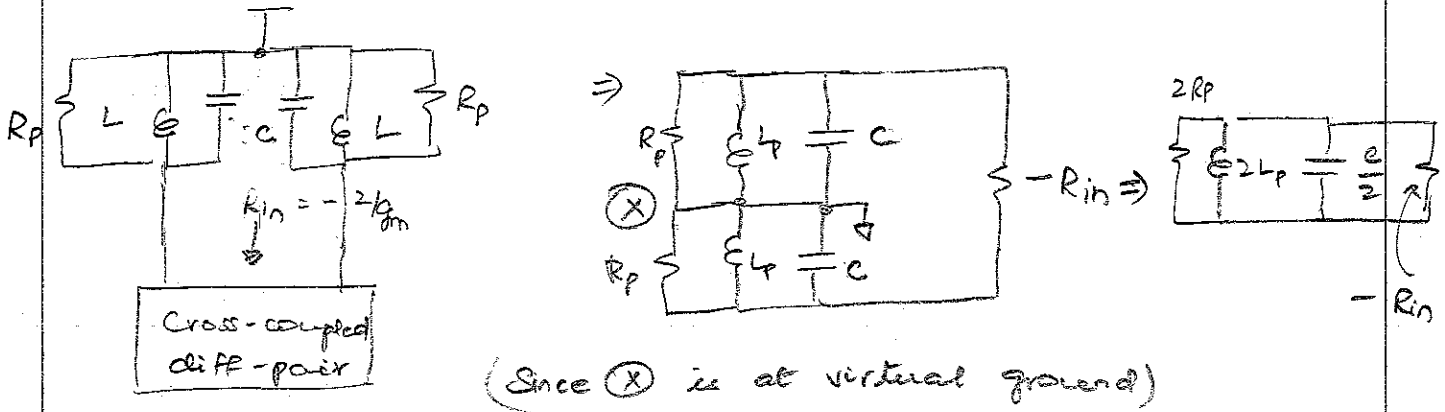
$$\Rightarrow v_1 = -v_2 = -(v_1 - v_x)$$

$$\Rightarrow v_x = 2v_1$$

$$\Rightarrow i_x = -g_m \frac{v_x}{2} \quad \text{or} \quad \boxed{C_{in} = \frac{i_x}{v_x} = -\frac{g_m}{2}}$$

$$\text{or} \quad \boxed{R_{in} = -\frac{2}{g_m}}$$

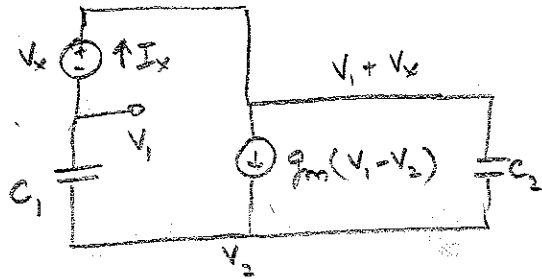
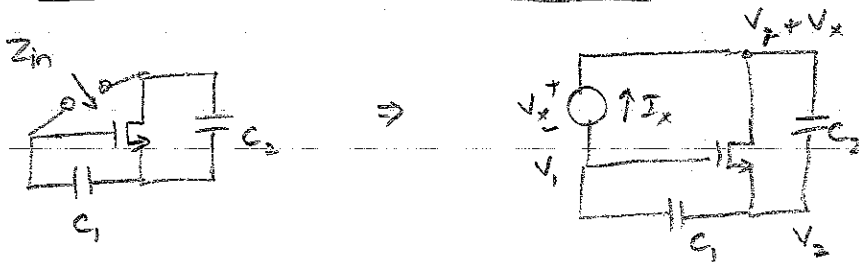
• In a negative- G_m cross coupled oscillator:



\Rightarrow Set $R_{in} = -2R_p$ for oscillation

$$\Rightarrow \frac{2}{g_m} = 2R_p \quad \text{or} \quad g_m R_p = 1$$

Single transistor oscillators:



$$\bullet V_1 = V_2 - I_x \frac{1}{sC_1}$$

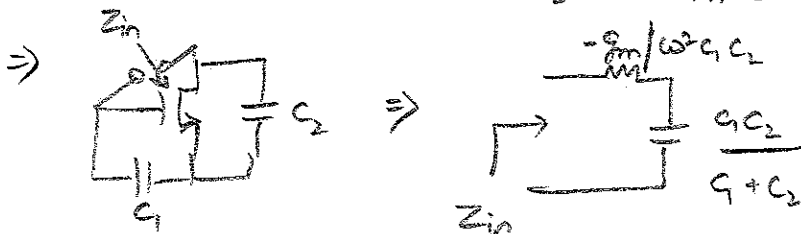
$$\Rightarrow V_1 - V_2 = \frac{-I_x}{sC_1}$$

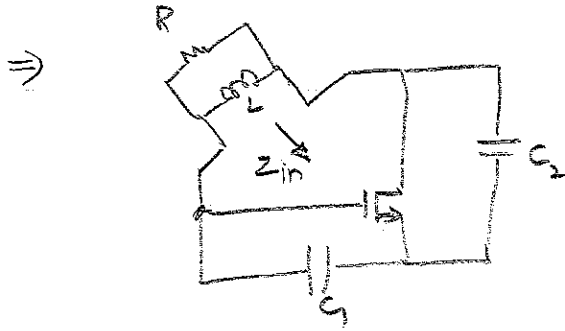
$$\bullet I_x = g_m (V_1 - V_2) + sC_2 (V_1 + V_x - V_2)$$

$$\Rightarrow I_x = g_m \left(\frac{-I_x}{sC_1} \right) + sC_2 \left(V_x - \frac{I_x}{sC_1} \right)$$

$$\Rightarrow V_x sC_2 = 1 + \frac{g_m}{sC_1} + \frac{C_2}{C_1} \quad \text{or} \quad V_x = \frac{1}{sC_1} + \frac{1}{sC_2} + \frac{g_m}{s^2 C_1 C_2}$$

$$\Rightarrow Z_{in}(j\omega) = \frac{-g_m}{\omega^2 C_1 C_2} + \frac{1}{sC_1 || C_2}$$



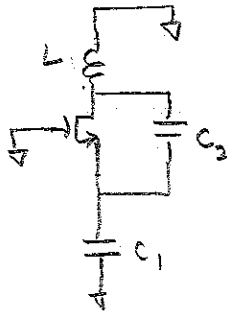


- For oscillation to start, we require

$$\frac{g_m}{\omega^2 C_1 C_2} \geq R$$

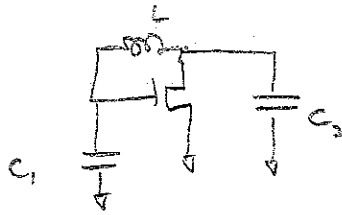
- can get 3 oscillator topologies by simply defining an AC ground:

Ground gate:

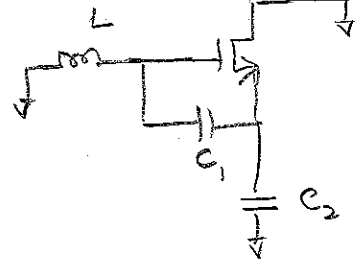


(COLPITTS)

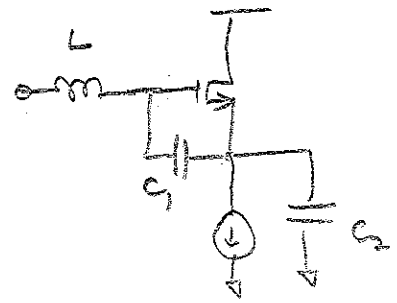
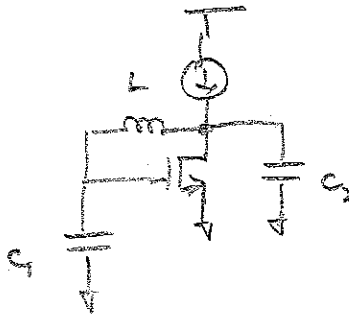
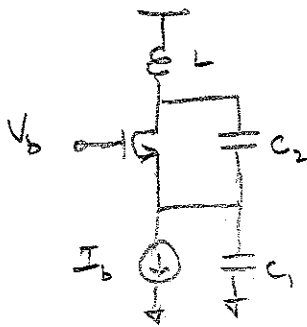
Ground source



Ground drain

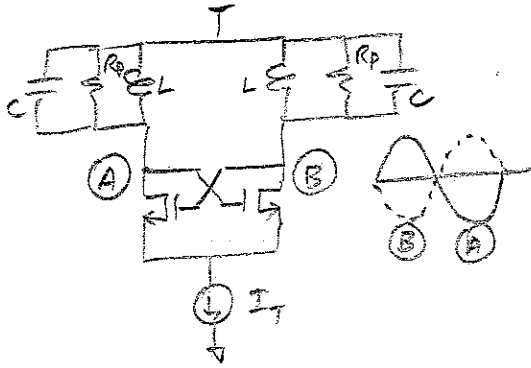


With biasing:



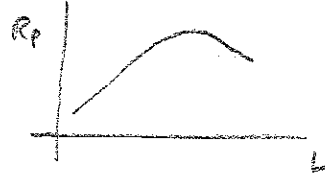
Amplitude of Oscillation & Start-up

1) Cross-coupled oscillator:



• Choose inductor for largest possible R_p

→ highest possible Q.

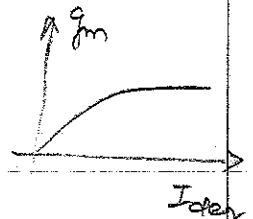


• choose I_T for large swing, and $(\frac{W}{L})$ of transistors to guarantee start-up:

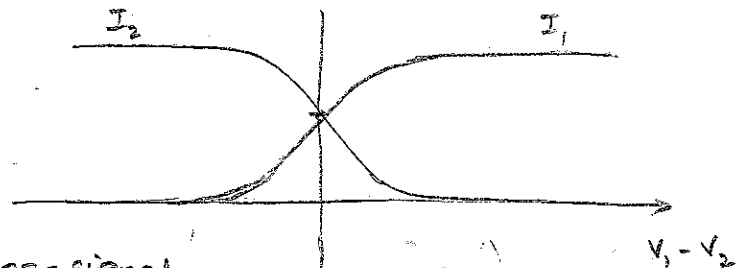
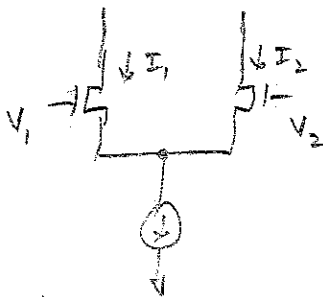
ie Small-signal $g_m > \frac{1}{R_p}$ (Rule of thumb: $g_m \approx \frac{2}{R_p}$)

Recall

$$g_m = \begin{cases} \frac{\mu_n C_{ox}}{2} \left(\frac{W}{L}\right) (V_{GS} - V_T) & \text{w/o vel. sat} \\ \frac{\mu_n C_{ox}}{2} \left(\frac{W}{L}\right) (L E_{sat}) & \text{with vel. sat} \end{cases}$$

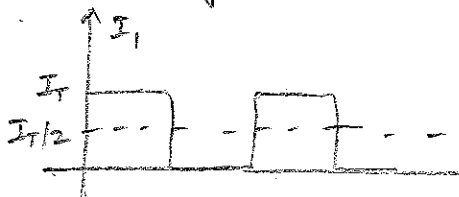


• For MOS diff pair:



Large-signal transconduct

$g_m(V)$



$$I_1 = I_T \left[\frac{1}{2} + \frac{2}{\pi} \left\{ \cos \omega_0 t - \frac{1}{3} \cos 3\omega_0 t + \dots \right\} \right]$$



→ Only fundamental component causes voltage @ tank output. (DC & harmonics get filtered)

⇒ Amplitude = $\frac{2}{\pi} I_T R_p$

⇒ Large signal transconductance

$$G_m = \frac{2}{\pi} I_T$$

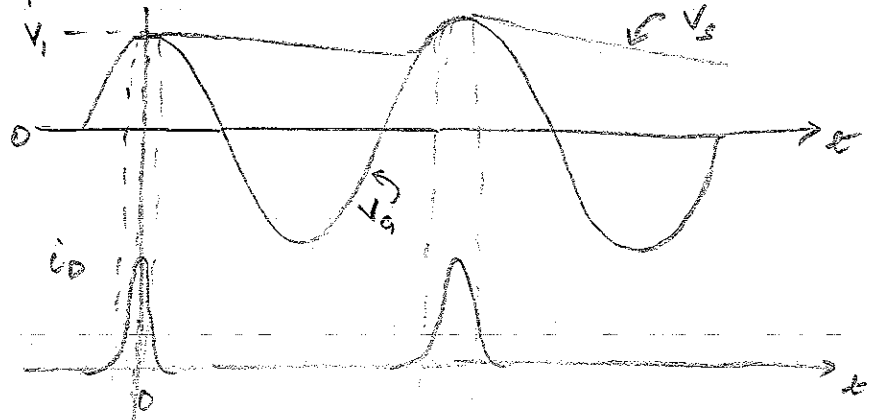
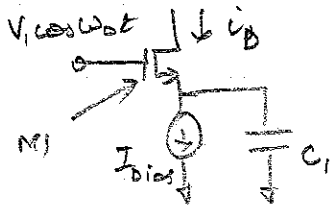
- Note that the oscillation amplitude is independent of the device size.

2) Colpitts Oscillator:

- First, derive large-signal transconductance of MOSFET

- Assume large-amplitude, high-frequency

input sinusoid.



- M1 conducts only when V_g is large. When V_g is not close to its peak, M1 cuts off and I_{bias} discharges C_s .
- Drain current waveform consists of slivers of current.
- Since i_D is periodic with frequency ω_0 , express as Fourier series:

$$i_D(t) = I_{DC} + \sum_{n=1}^{\infty} \hat{I}_n \cos n\omega_0 t$$

(pick the time reference $t=0$ as shown above. Then, all the $\sin n\omega_0 t$ terms drop out)

- Since C_s cannot draw a DC current, KCL at source gives $I_{DC} = I_{bias}$.

- Fundamental component $\hat{I}_1 = \frac{2}{T} \int_0^T i_D(t) \cos \omega_0 t dt \approx \frac{2}{T} \int_0^T i_D(t) dt$

$$\Rightarrow \hat{I}_1 = 2 I_{bias}$$



- If the drain current flows into a tank tuned to ω_0 only the fundamental component of i_D causes an appreciable voltage across the tank (high-order harmonics get filtered)

$$\Rightarrow \text{Large signal transconductance } G_m \approx \frac{\hat{I}_D}{V_1} = \frac{2I_{Bias}}{V_1}$$

- Compare G_m with g_m :

Recall short-channel model:

$$I_D = \frac{\mu_n C_{ox}}{2} \left(\frac{W}{L}\right) (V_{GS} - V_T) (V_{GS} - V_T) \parallel (L C_{fc})$$

$$\frac{\mu_n C_{ox}}{2} \left(\frac{W}{L}\right) (V_{GS} - V_T)^2 \quad (\text{no vel. sat})$$

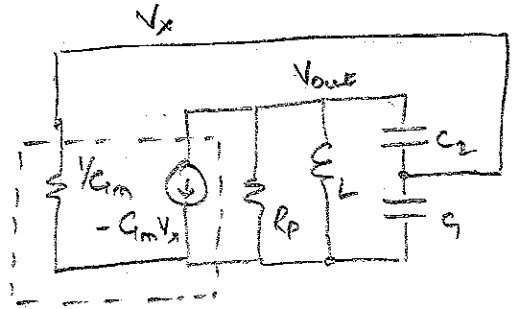
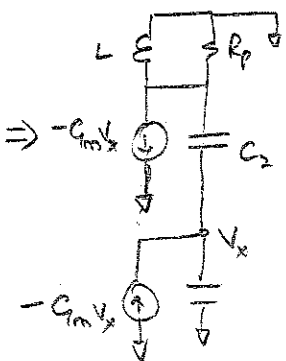
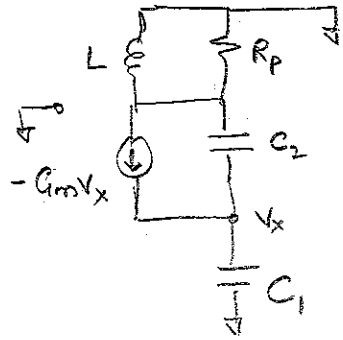
$$\frac{\mu_n C_{ox}}{2} \left(\frac{W}{L}\right) (V_{GS} - V_T) L C_{fc} \quad (\text{with vel. sat})$$

$$\Rightarrow \frac{2I_{Bias}}{V_{GS} - V_T} \leq g_m \frac{I_{Bias}}{V_{GS} - V_T}$$

(no vel. sat) (vel. sat)

$$\Rightarrow \frac{V_{DSat}}{V_1} \leq \frac{G_m}{g_m} \leq \frac{2V_{DSat}}{V_1}$$

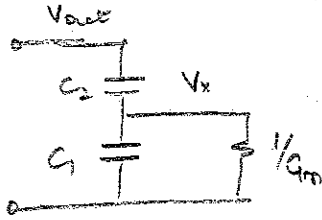
- Apply to Colpitts oscillator:



Large-signal transistor model

- Note that $G_m V_x = 2I_{Bias}$

Consider the capacitive divider:

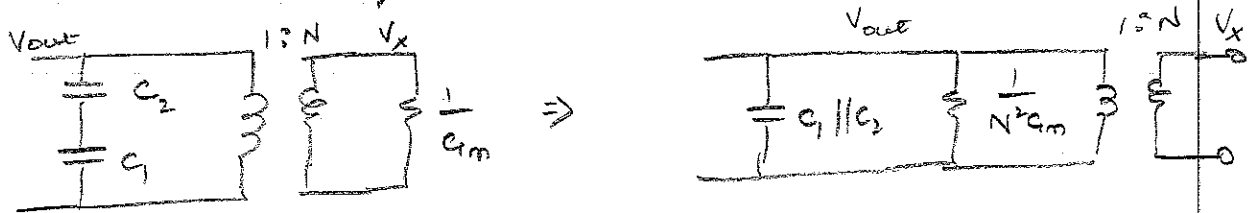


Assume that $1/g_m$ does not load the divider (ie $\frac{1}{\omega C_1} \ll \frac{1}{g_m}$, or equivalently,

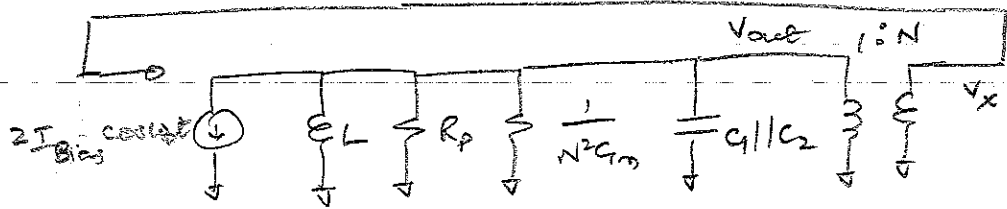
$$Q_1 = \omega C_1 \cdot \frac{1}{g_m} \gg 1$$

$$\Rightarrow V_x = \frac{C_2}{C_1 + C_2} V_{out} \leftarrow \text{transformer with turns ratio } N = \frac{C_2}{C_1 + C_2}$$

This leads to an equivalent circuit



\Rightarrow complete equivalent circuit is



For resonance, set $\omega_0 = \frac{1}{\sqrt{L C_1 \parallel C_2}}$

$$V_{out} = 2 I_{Bias} \cdot R_p \parallel \frac{1}{N^2 g_m} = \frac{2 I_{Bias} R_p}{N^2 g_m R_p + 1} \quad (g_m = \frac{2 I_{Bias}}{N V_{out}})$$

$$\Rightarrow V_{out} \left[1 + N^2 \cdot \frac{2 I_{Bias}}{N V_{out}} \cdot R_p \right] = 2 I_{Bias} R_p$$

$$\text{or } \boxed{V_{out} \approx 2 I_{Bias} (1 - N) R_p}$$

- Make R_p as large as possible (ie max Q)

- For best phase noise set $N \approx 0.2$ or $\boxed{\frac{C_2}{C_1} = 4}$